



60V P-Channel Trench Power MOSFET

General Description

The SJJ60P110 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

Features

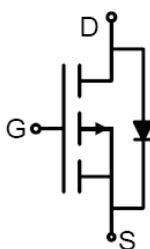
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handling capability
- Lead free product is acquired

Application

- Load Switch

Key Performance Parameters

Parameter	Value	Unit
V_{DS}	-60	V
$R_{DS(ON_TYP)}$	11.5	mΩ
I_D	-64	A
Q_G	140	nC



Schematic Diagram



TO-263 top view



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJJ60P110	SJJ60P110	TO-263	Tape	\	\	1000 Pcs

Table 1. Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	-60	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_C=25^\circ\text{C}$)	-64	A
	Drain Current-Continuous($T_C=100^\circ\text{C}$)	-41	A
I_{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-256	A
P_D	Maximum Power Dissipation($T_C=25^\circ\text{C}$)	96	W
	Maximum Power Dissipation($T_C=100^\circ\text{C}$)	38	W
E_{AS}	Avalanche energy (Note 2)	484	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.3	$^\circ\text{C/W}$



60V P-Channel Trench Power MOSFET

Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-60V, V _{GS} =0V T _J =25℃			-1	μA
		V _{DS} =-60V, V _{GS} =0V T _J =125℃			-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1		-2.5	V
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-20A		38		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-15A T _J =25℃		10.4	13.5	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-10A T _J =25℃		14	18.6	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-30V,V _{GS} =0V, f=1.0MHz		8700		pF
C _{oss}	Output Capacitance			290		pF
C _{rss}	Reverse Transfer Capacitance			210		pF
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =-10V, V _{DS} =-30V, R _L =1.5Ω, R _{GEN} =3Ω		26		nS
t _r	Turn-on Rise Time			21		nS
t _{d(off)}	Turn-Off Delay Time			138		nS
t _f	Turn-Off Fall Time			30		nS
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-30V, I _D =-20A		140		nC
Q _{gs}	Gate-Source Charge			19		nC
Q _{gd}	Gate-Drain Charge			28		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				-64	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =-20A			-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-20A, di/dt=100A/μs		56		ns
Q _{rr}	Reverse Recovery Charge	I _F =-20A, di/dt=100A/μs		63		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

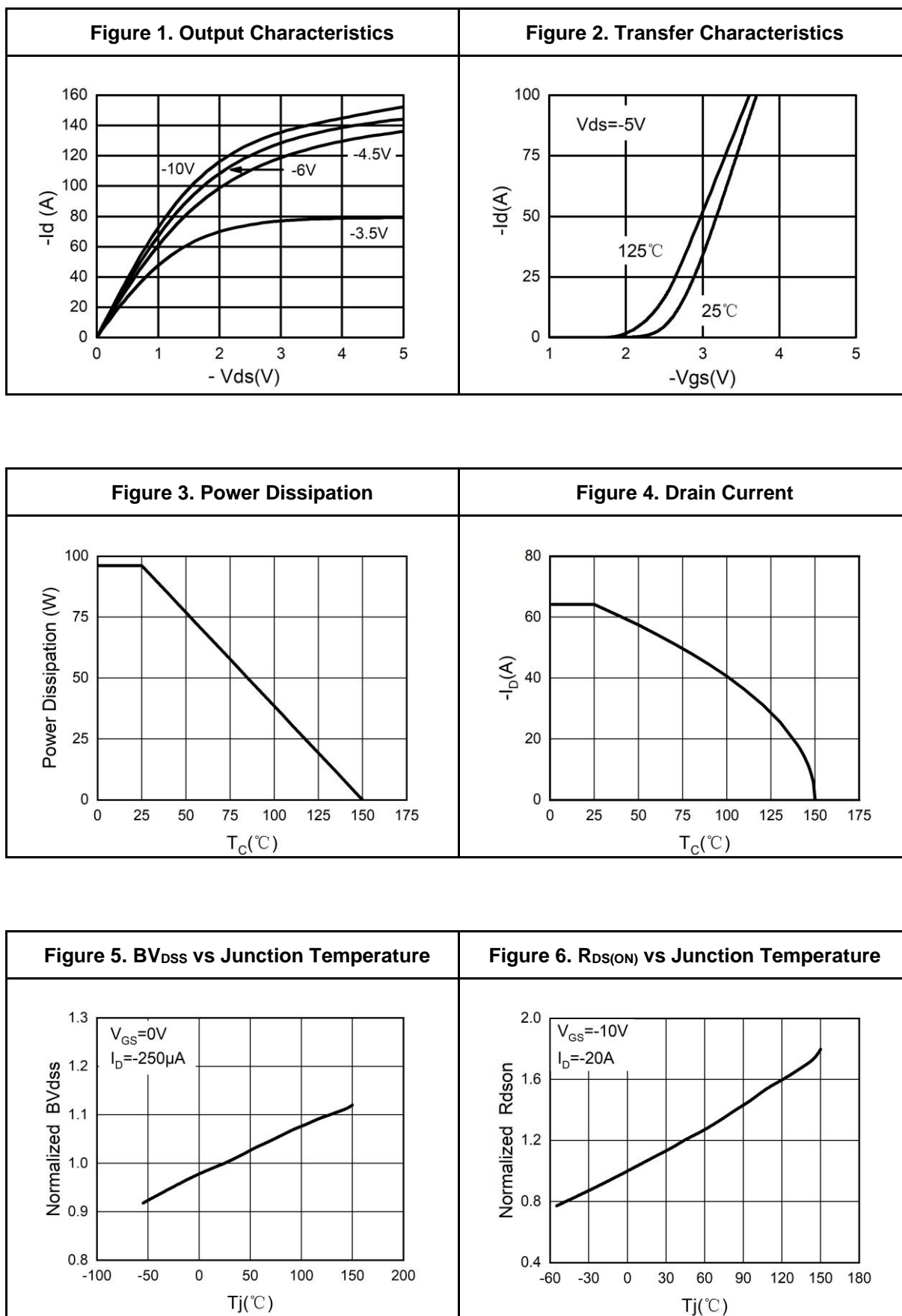
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=-40V, V_G=-10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



60V P-Channel Trench Power MOSFET

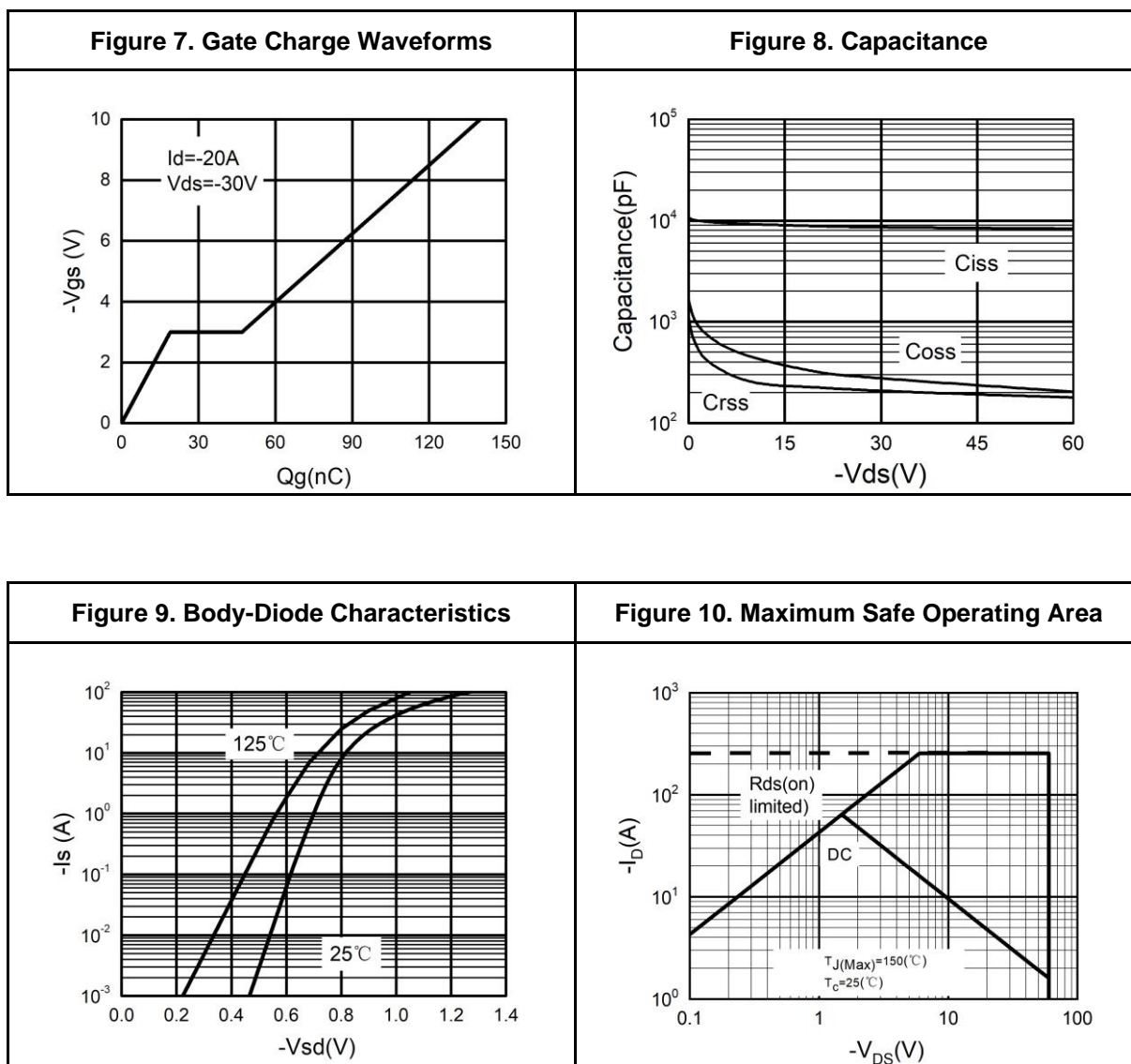
Typical Electrical And Thermal Characteristics (Curves)





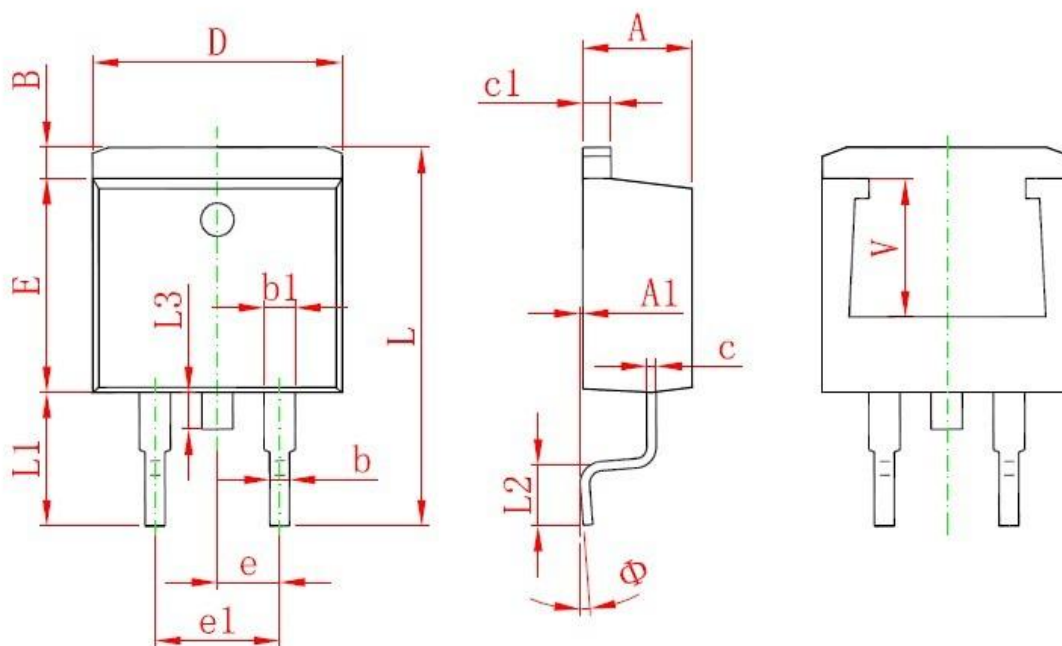
60V P-Channel Trench Power MOSFET

Typical Electrical And Thermal Characteristics (Curves)





TO-263 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Ma
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF.		0.220REF.	
Φ	0°	8°	0°	8°



60V P-Channel Trench Power MOSFET

Attention

This product described in this document can not be used in life support devices or systems, aircraft's control systems, and other applications whose failure can be reasonably expected to result in serious physical and/or material damage, apart from that when an application agreement is signed between customer and Wuxi Shangjia Semiconductor.

The performances and characteristics of this product in the independent testing state are displayed in this document. Wuxi Shangjia Semiconductor can't guarantee of the performances and characteristics of this described product that mounted in the customer's products or equipments as same as that in the independent testing state. So the customer should evaluate and test devices mounted in the customer's products or equipments.

Wuxi Shangjia Semiconductor reserves the right to improve the designs, functions and reliability of this product and modify any and all information described in this document without notice customer, apart from that when an notice agreement is signed between customer and Wuxi Shangjia Semiconductor.

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Wuxi Shangjia Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.